JST16A-1200SW 16A TRIAC **Rev.A.1.2**

DESCRIPTION:

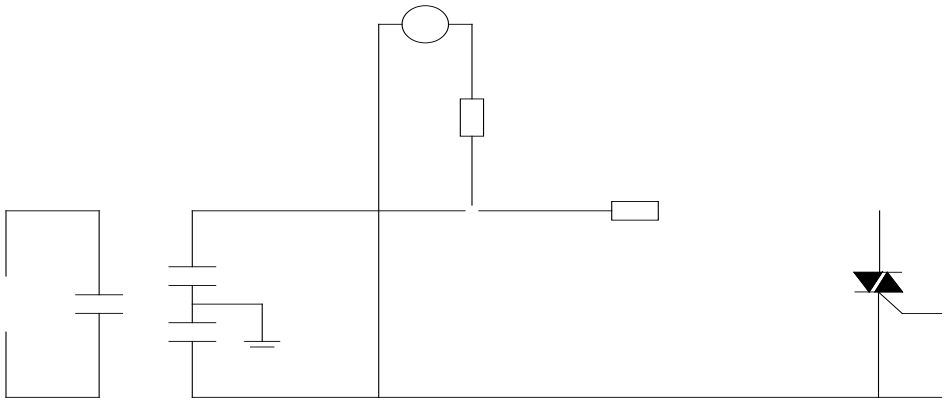
w -345A) Tue JST 16A-1200SW 339 Tc -0.4 87C56 484V-0.6-5 0 6d [()-326(0)]8.4.52 Tm8.4.5333. 5248.4

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

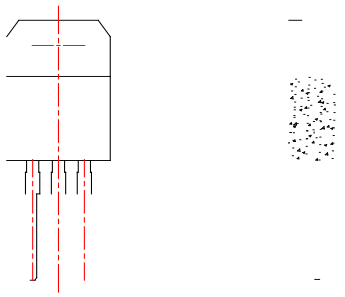
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	- -	- -	MAX.	10	mA
V	V_D =12V R_L =33Ω --				

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA



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